

3.46 PHOTONIC MATERIALS AND DEVICES

Lecture 14: Defects and Strain

Lecture

Notes

Perfection

- LRO (Long Range Order)
- SRO (Short Range Order)

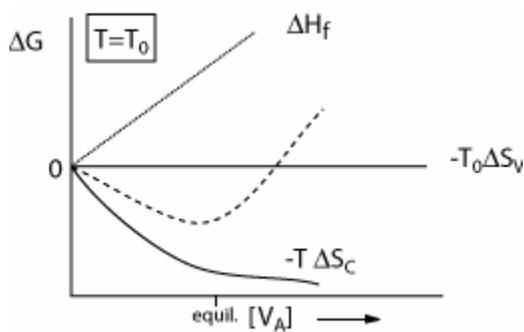
Imperfection

- Vibrating atom
- Electronic change
- Chemical impurity
- Point defect (I, V)
- 1D defect (dislocation)
- 2D defect (grain boundary)
- 3D defect (precipitate)

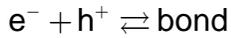
Defect Chemistry

$$\Delta G_f = \Delta H_f - T(\Delta S_v + \Delta S_c)$$

Vacancy Equilibria



Charge Carriers as Defects



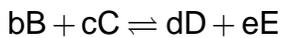
$$[e^-][h^+] = np = K_{np}$$

$$= \exp\left(-\frac{\Delta G}{k_B T}\right)$$

$$= \exp\left(\frac{\Delta S}{k_B}\right) \exp\left(-\frac{\Delta H}{k_B T}\right)$$

$$= N_C N_V \exp\left(-\frac{E_g}{k_B T}\right)$$

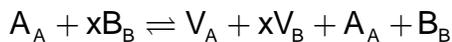
Point Defect Equilibria in Compounds



$$K = \frac{[D]^d [E]^e}{[B]^b [C]^c}$$

AB_x Compounds

Schottky Defect (vacancy pair)



$$K_S = [V_A][V_B]^x$$

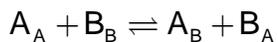
Frenkel Pair



$$K_{FP}(A) = [A_I][V_A]$$

$$K_{FP}(B) = [B_I][V_B]$$

Anti-Site Defect



$$K_{AS} = [A_B][B_A]$$

Nonstoichiometry

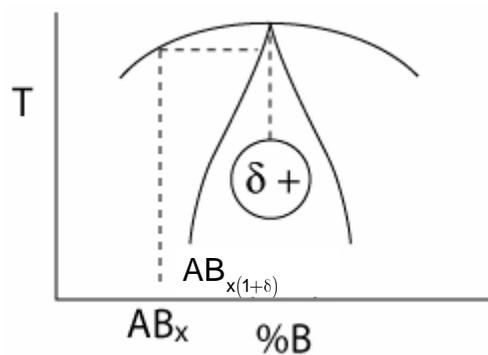
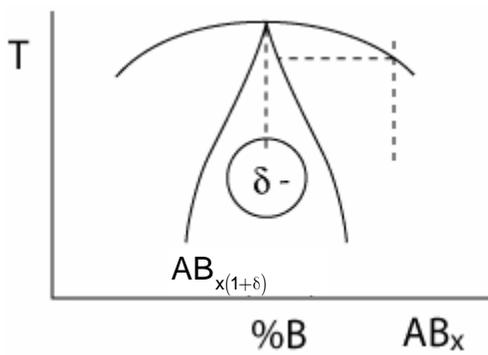


$$\frac{[A]}{[B]} \neq \frac{1}{x}$$



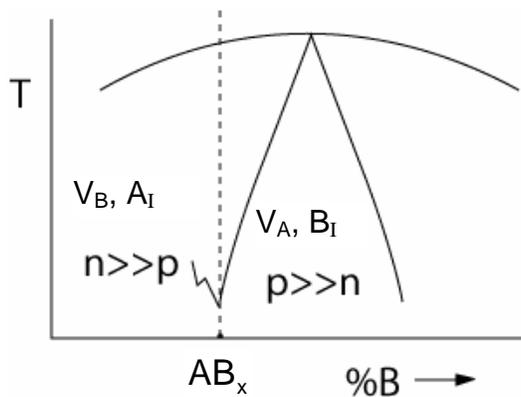
for a volatile component "B"

$$x\delta = [A_I] - [V_B] + [A_B]$$

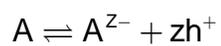
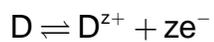


Electrical Properties: Defect Ion Approximation

A (metal)	B (non-metal)
excess A ($\delta < 0$)	excess B ($\delta > 0$)
V_B (donor)	V_A (acceptor)
A_I (donor)	B_I (acceptor)
A_B (acceptor)	B_A (donor)

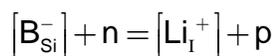
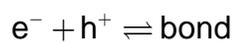
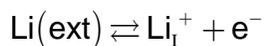
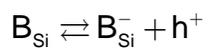


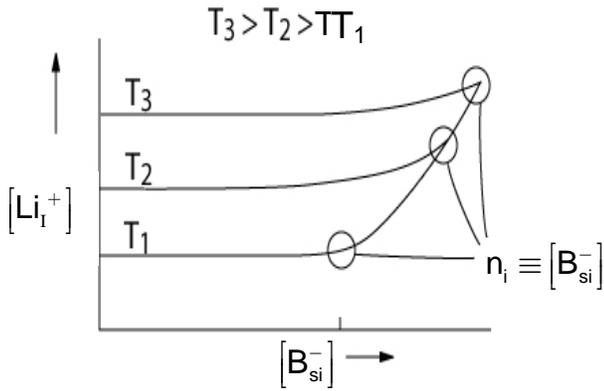
Defect-Carrier Equilibria



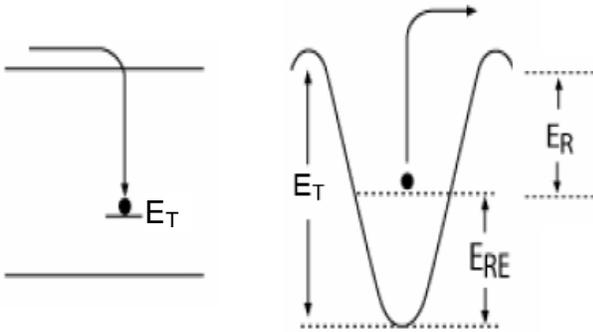
\Rightarrow solubility $\equiv f(E_F)$

example: Li in Si (B)





Consequences: Laser reliability



E_R : Recombination Energy
 E_T : Transition Energy
 E_{RE} : Reaction Enhanced Energy

$$\frac{R_{RE}}{R_T} = \frac{\eta R_R}{\nu_L} \exp\left[\frac{E_R}{k_B T}\right]$$

